

$$8600\text{\AA} - 0\text{\AA} + 300\text{\AA}$$

54C poly.

etch stop = thermal oxide 500\AA

P⁺ Si Substrate

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②

Post Mask - etch poly, stop on oxide

dep. ribbon = 850 \AA

$\text{SiN} = 850 \text{ \AA}$

poly.

Pt Si

Ribbon Photo and Etch.

substrate contact.

→ continue etch through.
 500 \AA oxide etch stop.

"posted out"

SiN

Sac
poly

ribbon
cut.

etch
stop.

after Etch - standard, aggressive resist strip
to clear polymer.

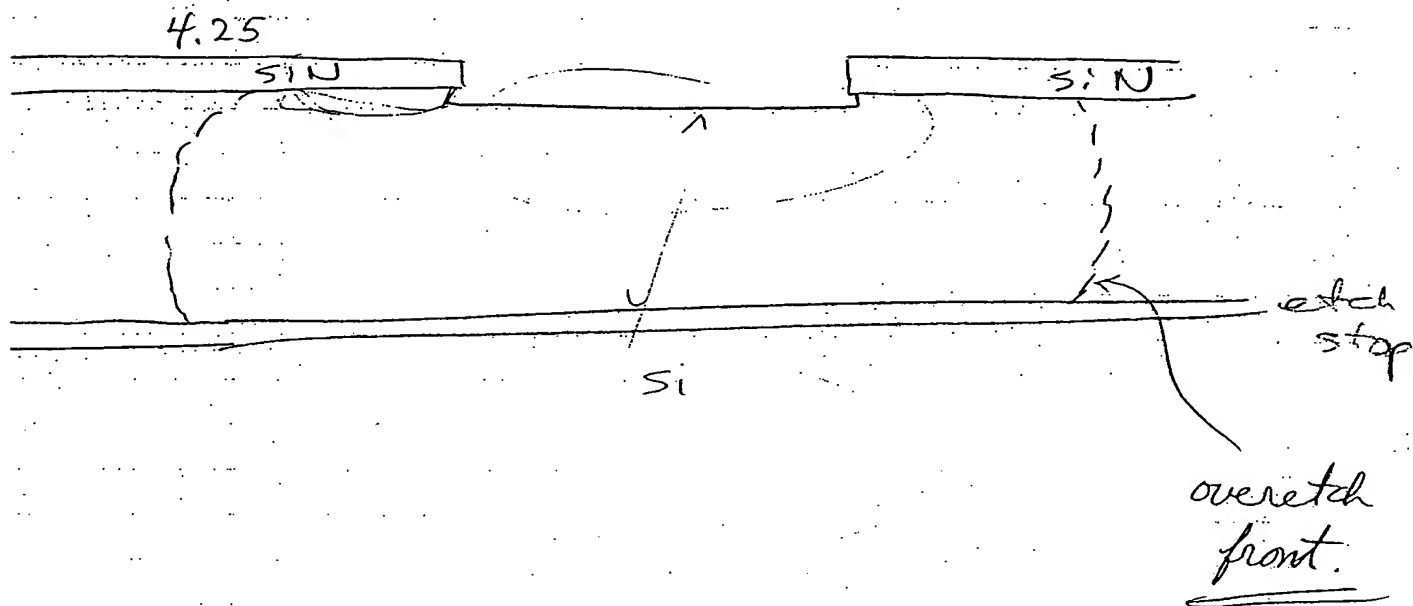
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M2 layer before partial release.

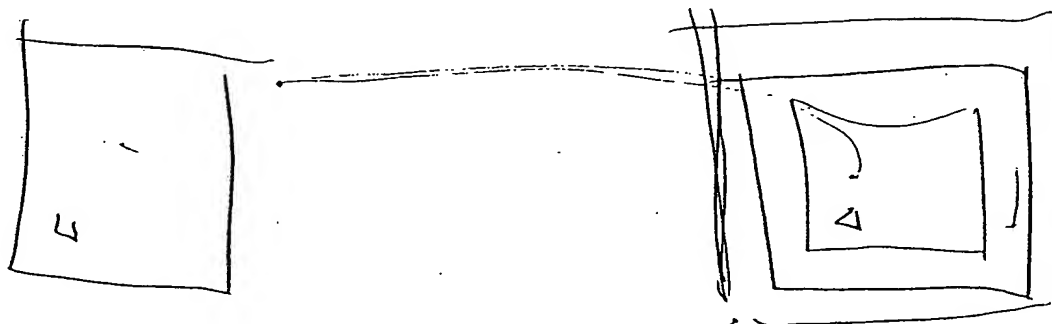
After ribbon etch & strip resist.

(3)

- partial XeF_2 release \rightarrow 2x to 1.5x overetch.



M2 ~~dep~~ - sputter Al pure - ~~3000~~ \AA
M2 photoetch.



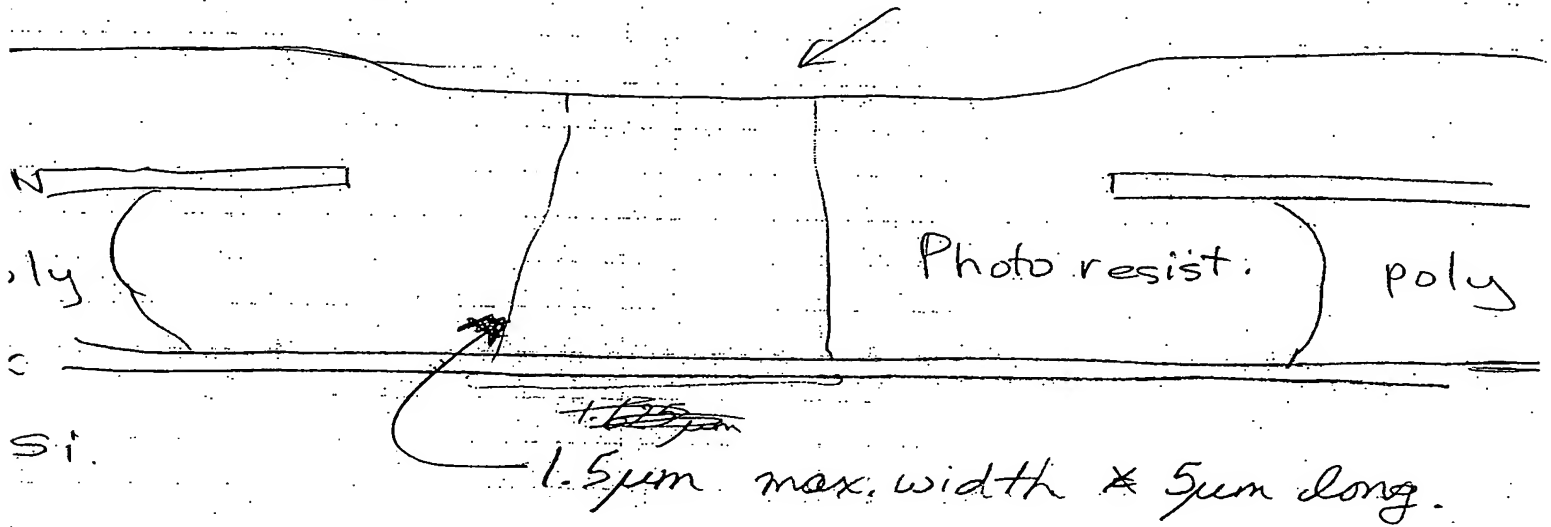
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Resist Dep

(4)

Via Photo

Via photo



Oxide etch 500 \AA into Silicon substrate.

Thin Al evap = 500 \AA

contact Anneal.

- "loosely" spaced die on wafer stepping.

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